EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	462	257/104.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:55
L2	182	257/109.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L3	1808	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L4	707	257/356.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L5	235	257/46.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L6	225	257/551.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L7	203	257/526.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:56
L8	40	257/527.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13

L9	50	1 and first adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:57
L10	26	2 and first adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:57
L11	64	1 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L12	36	2 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L13	375	3 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L14	147	4 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13
L15	13	5 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L16	52	6 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59

—

L17	40	7 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L18	7	8 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 20:59
L19	45	9 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L20	23	10 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L21	55	11 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L22	32	12 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L23	320	13 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L24	128	14 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00

L25	11	15 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L26	41	16 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:00
L27	15	17 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L28	4	18 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L29	17	19 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L30	14	20 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L31	17	21 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L32	15	22 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01

L33	155	23 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L34	56	24 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:01
L35	4	25 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L36	15	26 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:07
L37	4	27 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L38	2	28 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L39	6	29 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L40	8	30 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02

L41	6	31 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L42	9	32 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:02
L43	2	33 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:05
L44	2	34 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L45	1	35 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L46	1	36 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L47	0	37 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L48	0	38 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04

L49	1	39 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L50	1	40 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) with (trench or via or hole or concavity) with (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:04
L51	4	33 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:07
L52	2	34 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L53	3	35 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L54	1	36 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L55	0	37 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L56	0	38 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06

L57	2	39 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L58	3	40 and (second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type)) same (trench or via or hole or concavity) same (electrode or cathode or anode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:06
L59	120	257/606.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13
L60	27	59 and first adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13
L61	24	60 and second adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13
L62	12	61 and third adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:13
L63	6	62 and fourth adj (semiconductor or impurity or doped or ("N" adj type) or ("P" adj type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 21:14